Sheet _1_ of _1_													
IN TRIMATION DISCLOSURE CITATION				Docket Number (Optional) FUJ1:200A ) SERIAL NO.: 10/646,590									
(Use several spects if necessary) MAY 2 6 2004				APPLICANT(s) Takashi KOBAYASHI et al.									
				FILING DATE: August 22, 2003	Group Art Unit 2826								
U.S. PATENT DOCUMENTS													
EXAMINER INITIAL	REF	DOCUMENT NUMBER	DATE	NAME CLASS SUBCLASS		SUBCLASS	FILING DATE IF APPROPRIATE						
VAMS	US	4,602,266 A	7/86	Coe	357	20							
VAMS	US	5,345,101 A	6/94	Tu	257	495							
				·			/						
				·									
			-										
-								-					
	REF	DOCUMENT	DATE	FOREIGN PATENT DOCUMENTS  COUNTRY	CLASS	SUBCLASS	TRANSLATION						
MANI	GB	NUMBER 1427014 A	3/76	GB			YES	NO NO					
V/11 -													
_					. ,			<del>.</del>					
		,											
			TUES DOCU	MENT(S) (Including Author, Title, Date, Pert	Page Sto	<u> </u>		<u> </u>					
			THER DOCO	MENT(3) (Incloung Author, Title, Date, Peri	ment Pages, Etc.)								
\					•		<del></del>						
EXAMINED DATE CONSIDERED 9-1-04													

4 22 1

<sup>\*</sup>EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant,

	INFO	BMATION DISCLOSUR	E CITATION	Docket Number (Optional) FUJI: 200A Applicant(s)		Application Number 10/646,590		
		Pluse Several sheers if necess			Takashi KOBAYAS			
ł	/ ~	[5]		Filing Date August 22,	- 1	Group Art Unit		
	HOY	7 1 2002 %		U.S. PAT	ENT DOCUMENTS	2003		811
• ENAMINER INITIAL	The second	RADEMINENT NUMBER -	DATE		NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
VAM	T = T	4,412,242	10/83	Hermai	n et al.	357	52	
	US	4,399,449	8/83	Herma	n et al.	357	53	
	US	5,338,961	8/94	Lidow et al.		257	342	
	us	6,476,456	11/02	Boden, Jr.		257	486	
$I_{\perp}$	US	6,1144726	9/00	Barkhordarian		257	341	
	US	4,809,045	2/89 Yili		az	357	23.4	
	US	5,028,548	7/91 Nguy		en	437	15	
$\bigvee$	US 5,510,634		4/96 Okab		e et al.	257	139	
				FOREIG	N PATENT DOCUMENT	s		
	REF	DOCUMENT NUMBER	DATE		COUNTRY		SUBCLASS	YES NO
VAMS	EP	0 671 769 A2	9/95	EPO				
	EP	0 749 163 A2	12/96	EPO				
	EP	0 115 093 A2	8/84	ЕРО				
	GB	2 161 649 A	1/86	GB				
						-	Date, Pertinent Po	
MAN	1	"Optimization and Sur July 1991; IEEE Trans	face Charge Sen actions on Electi	sitivity of H ron Devices	igh-Voltage Blocking S , Vol. 38, No. 7; pages 10	tructures with 1 666-1675.	Shallow Junctio	ns''; Hamza Yilmaz
VIII		· · · · · · · · · · · · · · · · · · ·	C Danier - Name - Control	U. Ch.	a Han Bassades and C	o Conformer	(Dag Day - P	lant-naice
VAN	15	"A Parametric Study of Specialists, 1979 IEEE;	pages 385-395.	"; Cnenmin	g Hu; Proceedings of th	e Conterence o	T Rec. Power El	ectronics
EXAMINE	R ( )	ctor A. Mand	ala 9		DATE CONSIDERED	-04		
EXAMINE not conside	R: Initial	if citation considered, whether ude copy of this form with next	or not citation is in communication to	n conforman applicant.			ugh citation if no	in conformance and
	9.80							

Form PTO-A820 (also form PTO-1449) P09A/REV04

Patent and Trademark Office \* U.S. DEPARTMENT OF COMMERCE